TOSHIBA Multi Chip Discrece Device

HN4G01J

Audio Frequency General Purpose Amplifier Applications

Q1

• Small package (Dual type)

High voltage and high current

: $V_{CEO} = 50V$, $I_{C} = 150mA (max)$

• High h_{FE}: h_{FE} = 120~400

Excellent h_{FE} linearity

: $h_{FE} (I_C = 0.1 \text{mA}) / h_{FE} (I_C = 2 \text{mA}) = 0.95 \text{ (typ.)}$

Q2

Incorporating a bias resistor into a transistor reduces parts count.
 Reducing the parts count enable the manufacture of ever more compact equipment and save assembly cost.

Q1:2SC4837F Q2:RN1103F

Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	٧
Collector-emitter voltage	V_{CEO}	50	٧
Emitter-base voltage	V_{EBO}	5	V
Collector current	IC	150	mA
Base current	Ι _Β	30	mA

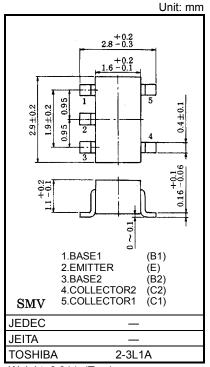
Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	10	V
Collector current	IC	100	mA

Maximum Ratings (Ta = 25°C) (Q1,Q2Common)

Characteristic	Symbol	Rating	Unit
Collector power dissipation	P _C *	300	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	_55~150	°C

^{*}Total rating.



Weight: 0.014g(Typ.)

Electrical Characteristics (Ta = 25° C) (Q1)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 60 \text{ V}, I_{E} = 0$	_	_	0.1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	0.1	μА
DC current gain	h _{FE}	$V_{CE} = 6 \text{ V}, I_{C} = 2 \text{ mA}$	120	_	400	
Collector-emitter saturation voltage	V _{CE (sat)}	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$	_	0.1	0.25	V
Transition frequency	f _T	$V_{CE} = 10 \text{ V}, I_{C} = 1 \text{ mA}$	60	_	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	2.0	_	pF

Electrical Characteristics (Ta = 25°C) (Q2)

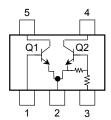
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 50 \text{ V}, I_{E} = 0$	_	_	100	nA
	I _{CEO}	$V_{CE} = 50 \text{ V}, I_B = 0$	_	_	500	
Emitter cut-off current	I _{EBO}	$V_{EB} = 10 \text{ V}, I_{C} = 0$	0.17	_	0.33	mA
DC current gain	h _{FE}	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$	70	_	_	
Collector-emitter saturation voltage	V _{CE} (sat)	$I_C = 5 \text{ mA}, I_B = 0.25 \text{ mA}$	_	0.1	0.3	V
Input voltage (ON)	V _{I (ON)}	$V_{CE} = 0.2 \text{ V}, I_{C} = 5 \text{ mA}$	1.3	_	3.0	V
Input voltage (OFF)	V _{I (OFF)}	$V_{CE} = 5 \text{ V}, I_{C} = 0.1 \text{ mA}$	1.0	_	1.5	V
Transition frequency	f _T	V _{CE} = 10 V, I _C = 5 mA	_	250	_	MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	_	3	_	pF
Input resistor	R1	_	15.4	22	28.6	kΩ
Resistor ratio	R1/R2	_	0.9	1.0	1.1	

Marking

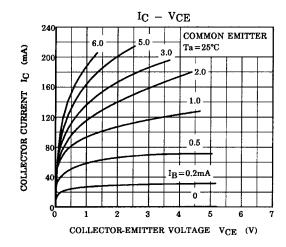


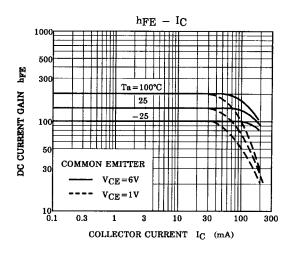
Equivalent Circuit (top view)

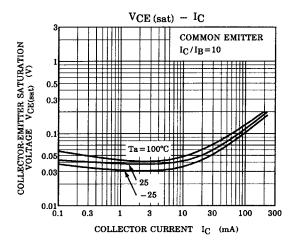
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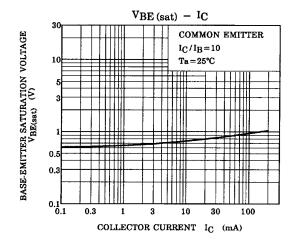


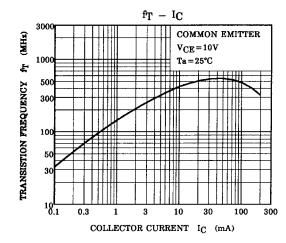
Q1

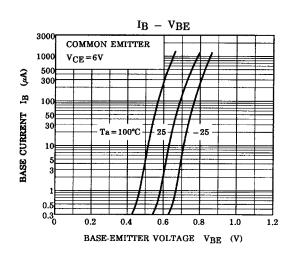




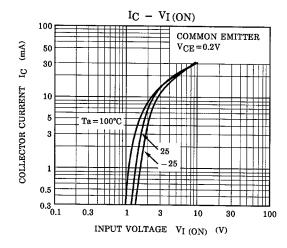


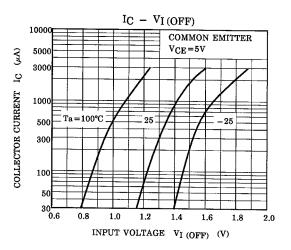


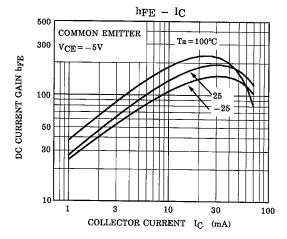


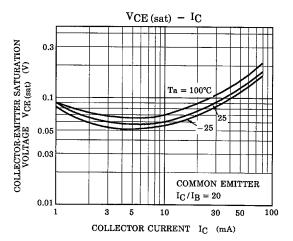


Q2

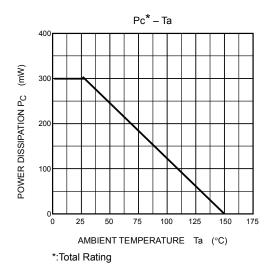








Q1,Q2 Common



2004-03-01

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